

**6A, 400V - 600V Hyperfast Dual Diodes**

RHRP640CC, RHRP650CC and RHRP660CC are hyperfast dual diodes with soft recovery characteristics ( $t_{rr} < 30ns$ ). They have half the recovery time of ultrafast diodes and are silicon nitride passivated ion-implanted hepaticas planar construction.

These devices are intended for use as freewheeling/clamping diodes and rectifiers in a variety of switching power supplies and other power switching applications. Their low stored charge and ultrafast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

Formerly developmental type TA49057.

**Ordering Information**

PART NUMBER	PACKAGE	BRAND
RHRP640CC	TO-220AB	RHRP640C
RHRP650CC	TO-220AB	RHRP650C
RHRP660CC	TO-220AB	RHRP660C

NOTE: When ordering, use the entire part number.

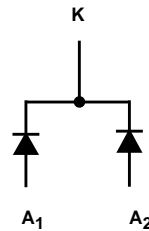
**Features**

- Hyperfast with Soft Recovery .....<30ns
- Operating Temperature ..... 175°C
- Reverse Voltage Up To.....600V
- Avalanche Energy Rated
- Planar Construction
- Related Literature
  - TB334 "Guidelines for Soldering Surface Mount Components to PC Boards"

**Applications**

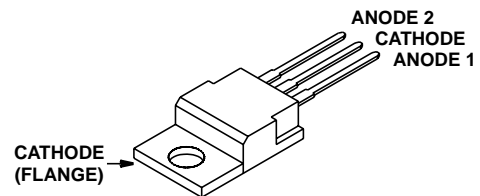
- Switching Power Supplies
- Power Switching Circuits
- General Purpose

**Symbol**



**Package**

JEDEC TO-220AB



## RHRP640CC, RHRP650CC, RHRP660CC

### Absolute Maximum Ratings (Per Leg) $T_C = 25^\circ\text{C}$ , Unless Otherwise Specified

	RHRP640CC	RHRP650CC	RHRP660CC	UNITS	
Peak Repetitive Reverse Voltage . . . . .	$V_{RRM}$	400	500	600	V
Working Peak Reverse Voltage . . . . .	$V_{RWM}$	400	500	600	V
DC Blocking Voltage . . . . .	$V_R$	400	500	600	V
Average Rectified Forward Current . . . . .	$I_{F(AV)}$	6	6	6	A
$T_C = 152^\circ\text{C}$					
Repetitive Peak Surge Current . . . . .	$I_{FSM}$	12	12	12	A
Square Wave, 20kHz					
Nonrepetitive Peak Surge Current . . . . .	$I_{FSM}$	60	60	60	A
Halfwave, 1 phase, 60Hz					
Maximum Power Dissipation . . . . .	$P_D$	50	50	50	W
Avalanche Energy (See Figures 10 and 11) . . . . .	$E_{AVL}$	10	10	10	mJ
Operating and Storage Temperature . . . . .	$T_{STG}, T_J$	-65 to 175	-65 to 175	-65 to 175	$^\circ\text{C}$
Maximum Temperature for Soldering					
Leads at 0.063in (1.6mm) from Case for 10s . . . . .	$T_L$	300	300	300	$^\circ\text{C}$
Package Body for 10s, see Tech Brief 334 . . . . .	$T_{pk}$	260	260	260	$^\circ\text{C}$

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

### Electrical Specifications (Per Leg) $T_C = 25^\circ\text{C}$ , Unless Otherwise Specified

SYMBOL	TEST CONDITION	RHRP640CC			RHRP650CC			RHRP660CC			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
$V_F$	$I_F = 6\text{A}$	-	-	2.1	-	-	2.1	-	-	2.1	V
	$I_F = 6\text{A}, T_C = 150^\circ\text{C}$	-	-	1.7	-	-	1.7	-	-	1.7	V
$I_R$	$V_R = 400\text{V}$	-	-	100	-	-	-	-	-	-	$\mu\text{A}$
	$V_R = 500\text{V}$	-	-	-	-	-	100	-	-	-	$\mu\text{A}$
	$V_R = 600\text{V}$	-	-	-	-	-	-	-	-	100	$\mu\text{A}$
	$V_R = 400\text{V}, T_C = 150^\circ\text{C}$	-	-	500	-	-	-	-	-	-	$\mu\text{A}$
	$V_R = 500\text{V}, T_C = 150^\circ\text{C}$	-	-	-	-	-	500	-	-	-	$\mu\text{A}$
	$V_R = 600\text{V}, T_C = 150^\circ\text{C}$	-	-	-	-	-	-	-	-	500	$\mu\text{A}$
$t_{rr}$	$I_F = 1\text{A}, dI_F/dt = 200\text{A}/\mu\text{s}$	-	-	30	-	-	30	-	-	30	ns
	$I_F = 6\text{A}, dI_F/dt = 200\text{A}/\mu\text{s}$	-	-	35	-	-	35	-	-	35	ns
$t_a$	$I_F = 6\text{A}, dI_F/dt = 200\text{A}/\mu\text{s}$	-	16	-	-	16	-	-	16	-	ns
$t_b$	$I_F = 6\text{A}, dI_F/dt = 200\text{A}/\mu\text{s}$	-	8.5	-	-	8.5	-	-	8.5	-	ns
$Q_{RR}$	$I_F = 6\text{A}, dI_F/dt = 200\text{A}/\mu\text{s}$	-	45	-	-	45	-	-	45	-	nC
$C_J$	$V_R = 10\text{V}, I_F = 0\text{A}$	-	20	-	-	20	-	-	20	-	pF
$R_{\theta JC}$		-	-	3	-	-	3	-	-	3	$^\circ\text{C}/\text{W}$

#### DEFINITIONS

- $V_F$  = Instantaneous forward voltage (pw = 300 $\mu\text{s}$ , D = 2%).
- $I_R$  = Instantaneous reverse current.
- $t_{rr}$  = Reverse recovery time (See Figure 9), summation of  $t_a + t_b$ .
- $t_a$  = Time to reach peak reverse current (See Figure 9).
- $t_b$  = Time from peak  $I_{RM}$  to projected zero crossing of  $I_{RM}$  based on a straight line from peak  $I_{RM}$  through 25% of  $I_{RM}$  (See Figure 9).
- $Q_{RR}$  = Reverse recovery charge.
- $C_J$  = Junction Capacitance.
- $R_{\theta JC}$  = Thermal resistance junction to case.
- pw = pulse width.
- D = duty cycle.

Typical Performance Curves

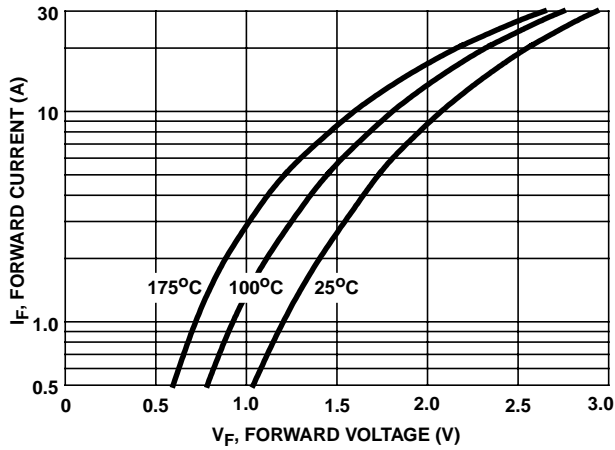


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

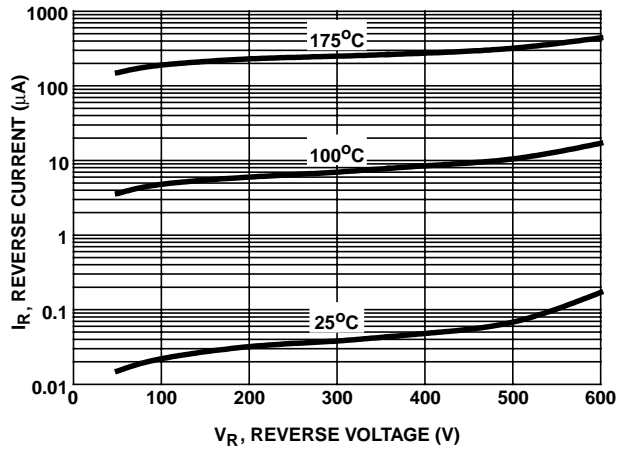


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

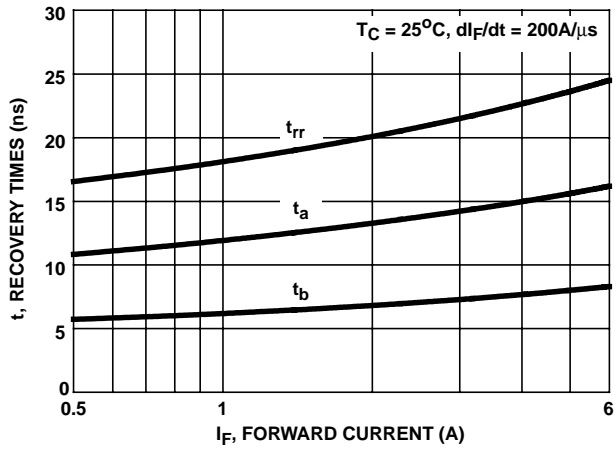


FIGURE 3.  $t_{rr}$ ,  $t_a$  AND  $t_b$  CURVES vs FORWARD CURRENT

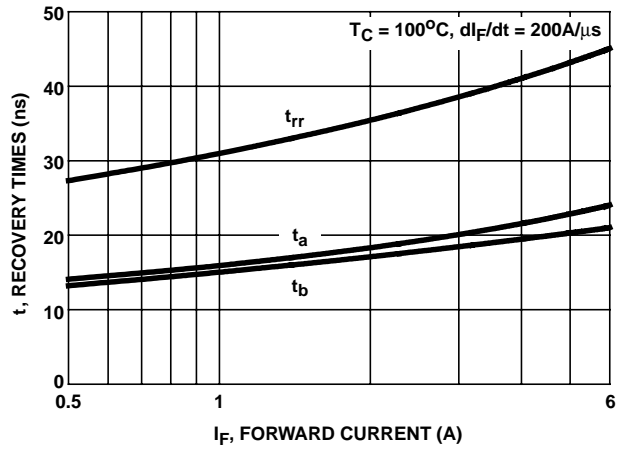


FIGURE 4.  $t_{rr}$ ,  $t_a$  AND  $t_b$  CURVES vs FORWARD CURRENT

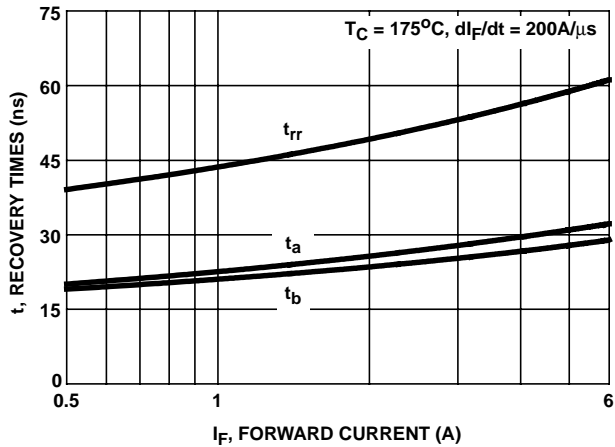


FIGURE 5.  $t_{rr}$ ,  $t_a$  AND  $t_b$  CURVES vs FORWARD CURRENT

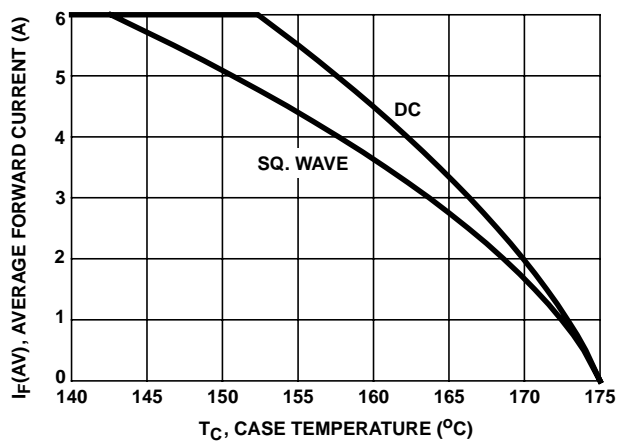


FIGURE 6. CURRENT DERATING CURVE

Typical Performance Curves (Continued)

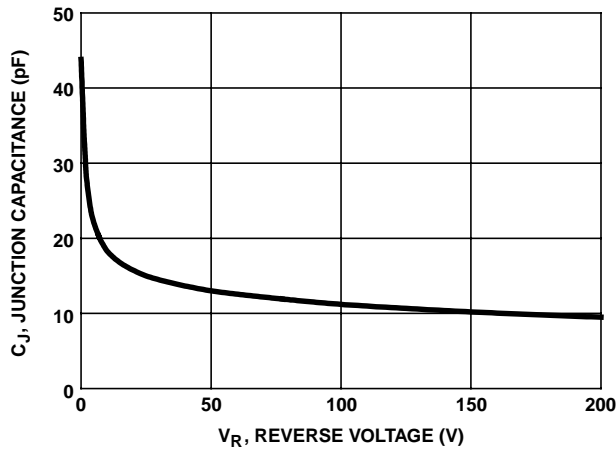


FIGURE 7. JUNCTION CAPACITANCE vs REVERSE VOLTAGE

Test Circuits and Waveforms

$V_{GE}$  AMPLITUDE and  
 $R_G$  CONTROL  $di_F/dt$   
 $t_1$  AND  $t_2$  CONTROL  $I_F$

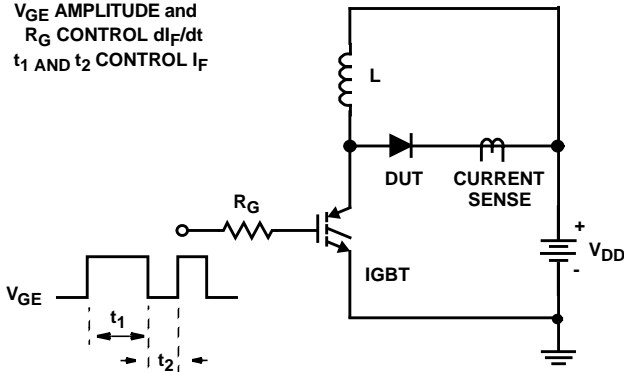


FIGURE 8.  $t_{rr}$  TEST CIRCUIT

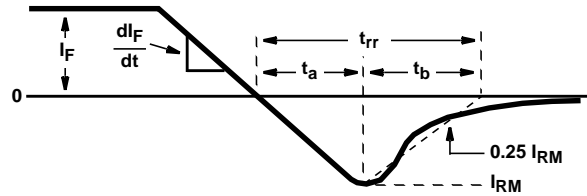


FIGURE 9.  $t_{rr}$  WAVEFORMS AND DEFINITIONS

$L = 20\text{mH}$   
 $R < 0.1\Omega$   
 $E_{AVL} = 1/2LI^2 [V_{R(AVL)}/(V_{R(AVL)} - V_{DD})]$   
 $Q_1 = \text{IGBT } (BV_{CES} > \text{DUT } V_{R(AVL)})$

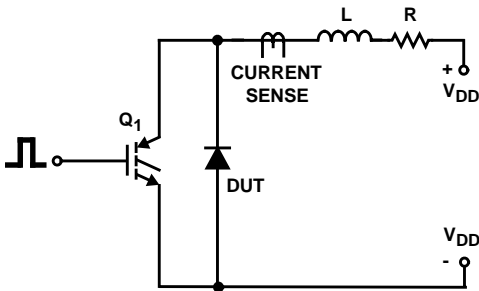


FIGURE 10. AVALANCHE ENERGY TEST CIRCUIT

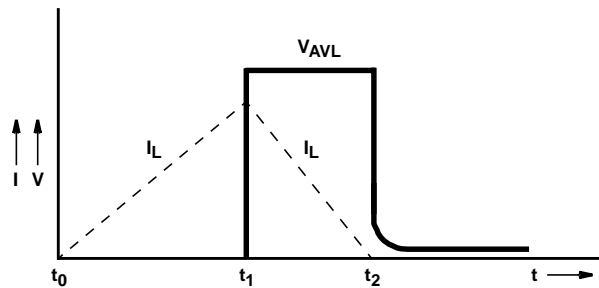


FIGURE 11. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

